

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

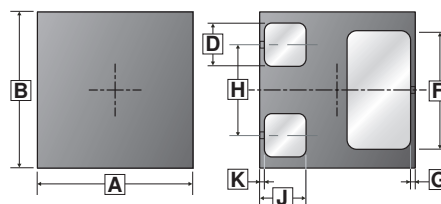
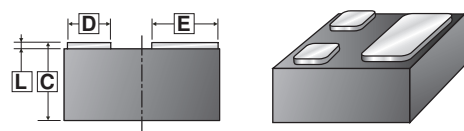
DESCRIPTION

- Epitaxial planar Silicon diode

WBFBP-03D

FEATURES

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance



APPLICATIONS

- For General Purpose Switching Applications , rectifiers
- For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

MARKING

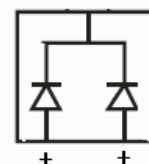
JJ

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.950	1.050	G	-	0.050
B	0.950	1.050	H	0.510	0.610
C	0.010	0.070	J	0.250	0.350
D	0.210	0.310	K	-	0.050
E	0.350 REF.		L	0.450	0.550
F	0.680 REF.				

PACKAGE INFORMATION

Package	MPQ	Leader Size
WBFBP-03D	5K	7 inch

TOP VIEW



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameters	Symbol	Rating	Unit
DC Blocking Voltage	V _R	85	V
Average Rectified Output Current	I _o	75	mA
Power Dissipation	P _D	100	mW
Operating Junction and Storage Temperature	T _J ,T _{STG}	150, -65~150	°C

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameters	Symbol	Min.	Max.	Unit	Test Conditions
Reverse breakdown voltage	$V_{(BR)}$	85	-	V	$I_R=100\mu\text{A}$
Maximum DC Reverse Current at rated DC blocking voltage	I_{R1}	-	2	μA	$V_R=75\text{V}$
	I_{R2}	-	0.03	μA	$V_R=25\text{V}$
Forward Voltage	V_{F1}	-	0.715	V	$I_F=1\text{mA}$
	V_{F2}	-	0.855	V	$I_F=10\text{mA}$
	V_{F3}	-	1	V	$I_F=50\text{mA}$
	V_{F4}	-	1.25	V	$I_F=150\text{mA}$
Diode Capacitance	C_D	-	1.5	pF	$V_R=0, f=1\text{MHz}$
Maximum Reverse Recovery Time	T_{RR}	-	4	nS	$I_F=I_R=10\text{mA}$

CHARACTERISTIC CURVES

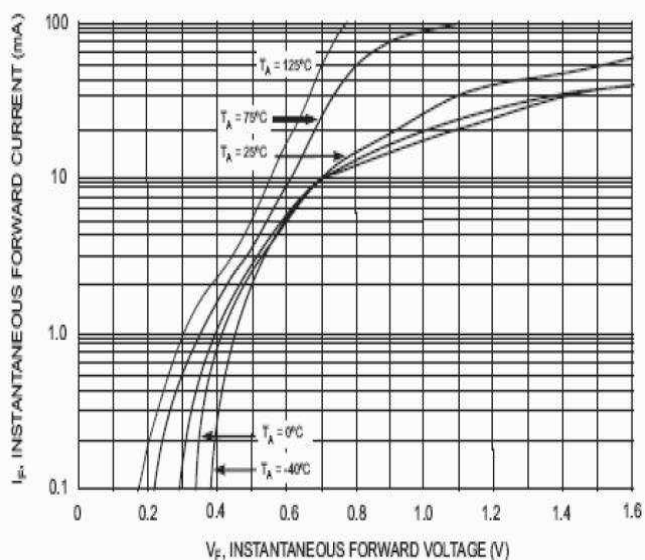


Fig. 1 Typical Forward Characteristics

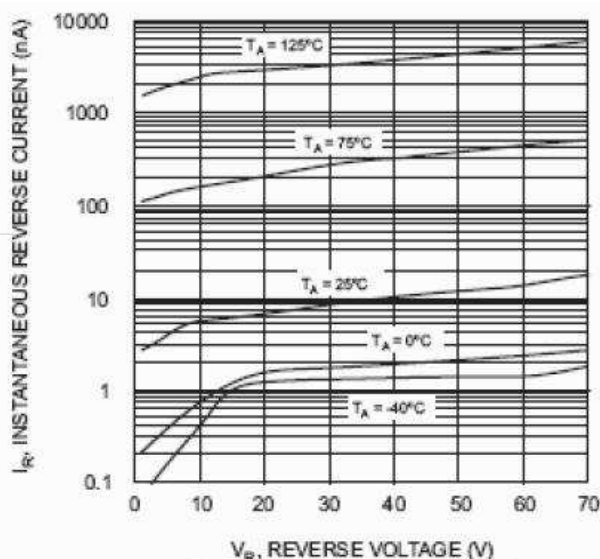


Fig. 2 Typical Reverse Characteristics

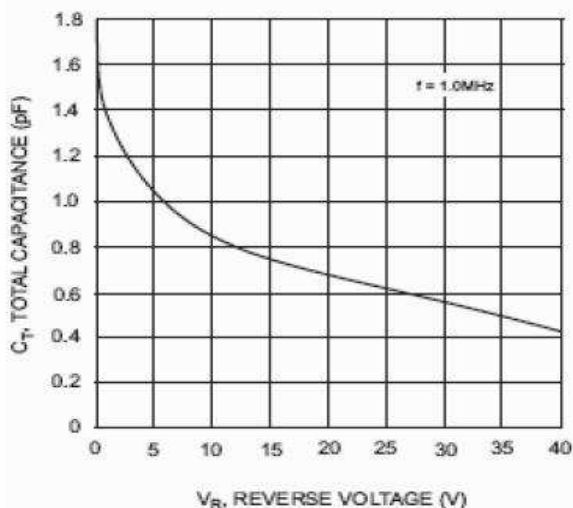


Fig. 3 Typical Capacitance

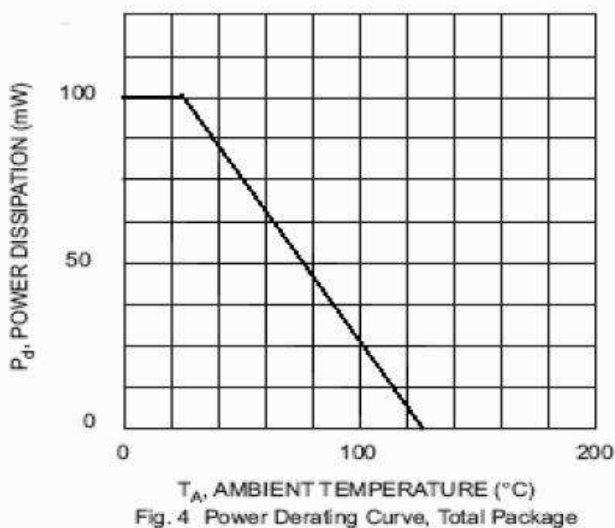


Fig. 4 Power Derating Curve, Total Package